

General Purpose Transistors

NPN Silicon

MMBT2222L, MMBT2222AL, SMMBT2222AL

Features

- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MAXIMUM RATINGS

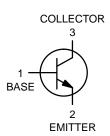
Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	V _{CEO}	30 40	Vdc
Collector-Base Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	V _{CBO}	60 75	Vdc
Emitter – Base Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	V _{EBO}	5.0 6.0	Vdc
Collector Current – Continuous	I _C	600	mAdc
Collector Current – Peak (Note 3)	I _{CM}	1100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
- 3. Reference SOA curve.





SOT-23 CASE 318 STYLE 6

MARKING DIAGRAM



xxx = 1P or M1B M = Date Code* • = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic			Symbol	Min	Max	Unit
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I _C = 10 mAdo	c, $I_B = 0$)	MMBT2222 MMBT2222A	V _{(BR)CEO}	30 40	_ _	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \mu Adc, I_I$	E = 0)	MMBT2222 MMBT2222A	V _{(BR)CBO}	60 75	- -	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C$	= 0)	MMBT2222 MMBT2222A	V _{(BR)EBO}	5.0 6.0	- -	Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	MMBT222	2A, SMMBT2222A	I _{CEX}	-	10	nAdc
Collector Cutoff Current ($V_{CB} = 50 \text{ Vdc}$, $I_{E} = 0$) ($V_{CB} = 60 \text{ Vdc}$, $I_{E} = 0$) ($V_{CB} = 50 \text{ Vdc}$, $I_{E} = 0$, $T_{A} = 125^{\circ}\text{C}$) ($V_{CB} = 60 \text{ Vdc}$, $I_{E} = 0$, $T_{A} = 125^{\circ}\text{C}$)		MMBT2222 2A, SMMBT2222A MMBT2222 2A, SMMBT2222A	Ісво	- - - -	0.01 0.01 10 10	μAdc
Emitter Cutoff Current (V _{EB} = 3.0 Vdc, I _C = 0)	MMBT222	2A, SMMBT2222A	I _{EBO}	-	100	nAdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vd	lc) MMBT222	2A, SMMBT2222A	I _{BL}	-	20	nAdc
ON CHARACTERISTICS				•		
DC Current Gain $ \begin{array}{l} \text{(I}_C = 0.1 \text{ mAdc, } V_{CE} = 10 \text{ Vdc)} \\ \text{(I}_C = 1.0 \text{ mAdc, } V_{CE} = 10 \text{ Vdc)} \\ \text{(I}_C = 10 \text{ mAdc, } V_{CE} = 10 \text{ Vdc)} \\ \text{(I}_C = 10 \text{ mAdc, } V_{CE} = 10 \text{ Vdc)} \\ \text{(I}_C = 10 \text{ mAdc, } V_{CE} = 10 \text{ Vdc, } T_A = -55^{\circ}\text{C)} \\ \text{(I}_C = 150 \text{ mAdc, } V_{CE} = 10 \text{ Vdc)} \text{ (Note 4)} \\ \text{(I}_C = 150 \text{ mAdc, } V_{CE} = 1.0 \text{ Vdc)} \text{ (Note 4)} \\ \text{(I}_C = 500 \text{ mAdc, } V_{CE} = 10 \text{ Vdc)} \text{ (Note 4)} \\ \end{array} $	MMBT2222	MMBT2222A only MMBT2222 2A, SMMBT2222A	h _{FE}	35 50 75 35 100 50 30 40	- - - 300 - -	-
Collector – Emitter Saturation Voltage (Note 4) (I _C = 150 mAdc, I _B = 15 mAdc)	MMBT222	MMBT2222 2A, SMMBT2222A	V _{CE(sat)}	- -	0.4 0.3	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MMBT222	MMBT2222 2A, SMMBT2222A		- -	1.6 1.0	
Base – Emitter Saturation Voltage (Note 4) (I _C = 150 mAdc, I _B = 15 mAdc)	MMBT222	MMBT2222 2A, SMMBT2222A	V _{BE(sat)}	_ 0.6	1.3 1.2	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MMBT222	MMBT2222 2A, SMMBT2222A		- -	2.6 2.0	
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain - Bandwidth Product (Note 5) (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	MMBT222	MMBT2222 2A, SMMBT2222A	f _T	250 300	_ _	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)			C _{obo}	-	8.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_{C} = 0$, $f = 1.0 \text{ MHz}$)	MMBT222	MMBT2222 2A, SMMBT2222A	C _{ibo}	- -	30 25	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz) (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		2A, SMMBT2222A 2A, SMMBT2222A	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)		2A, SMMBT2222A 2A, SMMBT2222A	h _{re}	- -	8.0 4.0	X 10 ⁻⁴
Small – Signal Current Gain ($I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, $f = 1.0$ kHz) ($I_C = 10$ mAdc, $V_{CE} = 10$ Vdc, $f = 1.0$ kHz)		2A, SMMBT2222A 2A, SMMBT2222A	h _{fe}	50 75	300 375	-

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

ELECTRICAL CHARACTERISTICS (TA = 25 C diffess office wise floted)		_		
Characteristic			Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS					
Output Admittance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ k}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ k}$)		h _{oe}	5.0 25	35 200	μmhos
Collector Base Time Constant (I _E = 20 mAdc, V _{CB} = 20 Vdc, f = 31.8 MHz) MMBT2222A, SMMBT2222A		rb, C _c	-	150	ps
Noise Figure (I _C = 100 μ Adc, V _{CE} = 10 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz) MMBT2222A, SMMBT2222A		NF	-	4.0	dB
SWITCHING CHARACTERISTICS (MMBT	2222A only)				
Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -0.5 \text{ Vdc},$	t _d	_	10	
Rise Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -0.5 \text{ Vdc}, \\ I_{C} = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc})$	t _r	_	25	ns
Storage Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 150 \text{ mAdc},$	t _s	-	225	200
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$	t _f	_	60	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 4. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.
- 5. f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

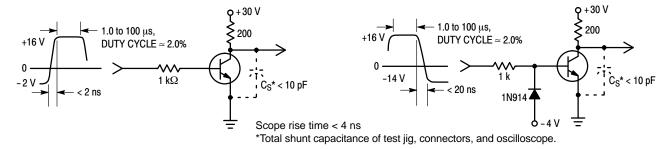


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

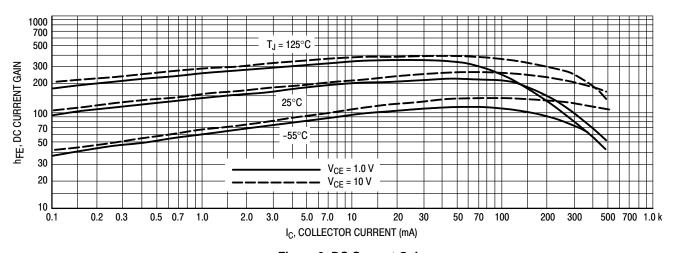


Figure 3. DC Current Gain

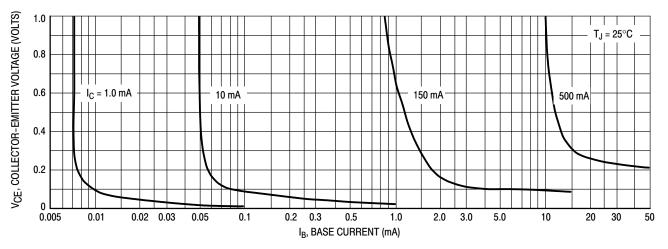


Figure 4. Collector Saturation Region

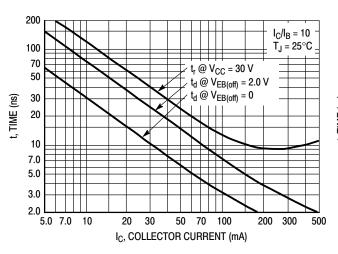


Figure 5. Turn-On Time

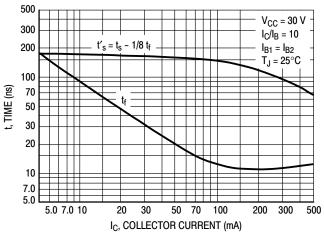


Figure 6. Turn-Off Time

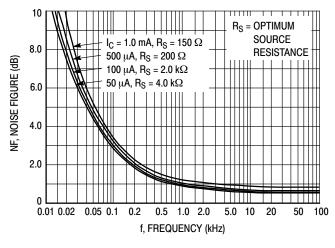


Figure 7. Frequency Effects

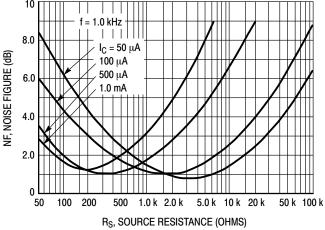
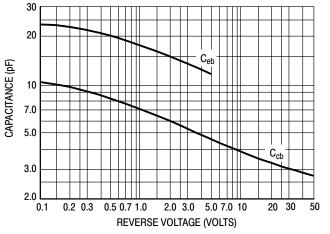


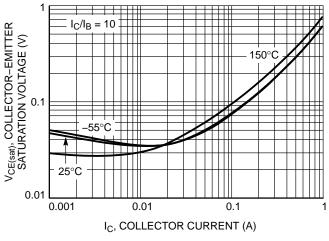
Figure 8. Source Resistance Effects



f_T, CURRENT-GAIN BANDWIDTH PRODUCT (MHz) 500 V_{CE} = 20 V $T_J = 25^{\circ}C$ 300 200 100 70 50 70 100 1.0 2.0 3.0 5.0 7.0 20 50 IC, COLLECTOR CURRENT (mA)

Figure 9. Capacitances

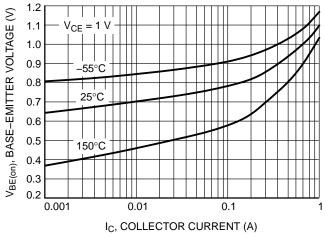
Figure 10. Current-Gain Bandwidth Product



1.3 1.2 $I_C/I_B = 10$ V_{BE(sat)}, BASE-EMITTER SATURATION VOLTAGE (V) 1.1 1.0 0.9 -55°C 0.8 25°C 0.7 0.6 150°C 0.5 0.4 0.3 0.2 0.001 0.01 0.1 I_C, COLLECTOR CURRENT (A)

Figure 11. Collector Emitter Saturation Voltage vs. Collector Current

Figure 12. Base Emitter Saturation Voltage vs.
Collector Current



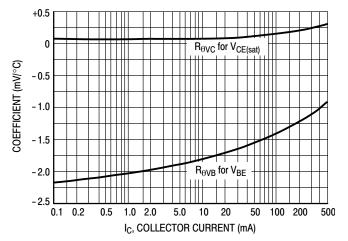


Figure 13. Base Emitter Voltage vs. Collector Current

Figure 14. Temperature Coefficients

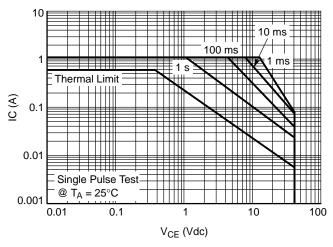


Figure 15. Safe Operating Area

ORDERING INFORMATION

Device	Specific Marking Code	Package	Shipping [†]
MMBT2222LT1G	M1B	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT2222ALT1G, SMMBT2222ALT1G	1P	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT2222LT3G	M1B	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBT2222ALT3G, SMMBT2222ALT3G	1P	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales